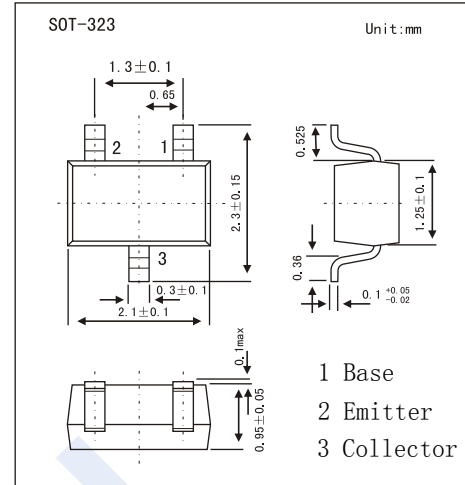


## NPN Transistors

## 2SC4562

## ■ Features

- High transition frequency  $f_T$ .
- Small collector output capacitance  $C_{ob}$ .
- Complementary to 2SA1748

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	50	V
Collector - Emitter Voltage	$V_{CEO}$	50	
Emitter - Base Voltage	$V_{EBO}$	5	
Collector Current - Continuous	$I_C$	50	mA
Collector Power Dissipation	$P_C$	150	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	50			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	50			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 40\text{V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current	$I_{CEO}$	$V_{CE} = 30\text{V}, I_B = 0$			1	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$		0.06	0.3	mV
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$			1.2	V
DC current gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 2\text{mA}$	200		500	
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		1.5		pF
Transition frequency	$f_T$	$V_{CB} = 10\text{V}, I_E = -2\text{mA}, f = 200\text{MHz}$		250		MHz

■ Classification of  $h_{FE}$ 

Type	2SC4562-Q	2SC4562-R
Range	200-400	250-500
Marking	AMQ	AMR

# NPN Transistors

## 2SC4562

■ Typical Characteristics

